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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/807,103	03/24/2004	Koichi Matsuda	03500.017972.	2515
	7590 03/11/200 CELLA HARPER &	EXAMINER		
30 ROCKEFEL	LER PLAZA	GARDNER, SHANNON M		
NEW YORK, NY 10112			ART UNIT	PAPER NUMBER
		1795		
			MAIL DATE	DELIVERY MODE
			03/11/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

## Advisory Action Before the Filing of an Appeal Brief

Application No.	Applicant(s)	
10/807,103	MATSUDA ET AL.	
Examiner	Art Unit	

	Shannon Gardner	1795					
The MAILING DATE of this communication appe	ars on the cover sheet with the c	orrespondence add	ress				
THE REPLY FILED <u>24 February 2009</u> FAILS TO PLACE THIS APPLICATION IN CONDITION FOR ALLOWANCE.							
1.  The reply was filed after a final rejection, but prior to or on application, applicant must timely file one of the following rapplication in condition for allowance; (2) a Notice of Appe for Continued Examination (RCE) in compliance with 37 C periods:	replies: (1) an amendment, affidavit al (with appeal fee) in compliance	, or other evidence, w with 37 CFR 41.31; or	hich places the (3) a Request				
a) The period for reply expires <u>3</u> months from the mailing date	of the final rejection.						
b) The period for reply expires on: (1) the mailing date of this Adno event, however, will the statutory period for reply expire la Examiner Note: If box 1 is checked, check either box (a) or (I MONTHS OF THE FINAL REJECTION. See MPEP 706.07(f	dvisory Action, or (2) the date set forth in ter than SIX MONTHS from the mailing b). ONLY CHECK BOX (b) WHEN THE	date of the final rejection	n.				
Extensions of time may be obtained under 37 CFR 1.136(a). The date of have been filed is the date for purposes of determining the period of extrunder 37 CFR 1.17(a) is calculated from: (1) the expiration date of the set forth in (b) above, if checked. Any reply received by the Office later may reduce any earned patent term adjustment. See 37 CFR 1.704(b). NOTICE OF APPEAL	, on which the petition under 37 CFR 1.1: ension and the corresponding amount of hortened statutory period for reply origin	of the fee. The appropria nally set in the final Office	ate extension fee e action; or (2) as				
2. The Notice of Appeal was filed on A brief in compl filing the Notice of Appeal (37 CFR 41.37(a)), or any exter Notice of Appeal has been filed, any reply must be filed wi	sion thereof (37 CFR 41.37(e)), to	avoid dismissal of the					
AMENDMENTS							
<ol> <li>The proposed amendment(s) filed after a final rejection, be (a) They raise new issues that would require further cor (b) They raise the issue of new matter (see NOTE below (c) They are not deemed to place the application in bett</li> </ol>	isideration and/or search (see NOT w);	E below);					
appeal; and/or (d) They present additional claims without canceling a c	orresponding number of finally reje	ected claims.					
NOTE: (See 37 CFR 1.116 and 41.33(a)).	M. Oan affacts of Nation of Name On		OTOL 004)				
<ol> <li>The amendments are not in compliance with 37 CFR 1.12</li> <li>Applicant's reply has overcome the following rejection(s):</li> </ol>		mpliant Amendment (I	310L-324).				
<ol> <li>Newly proposed or amended claim(s) would be all non-allowable claim(s).</li> </ol>		imely filed amendmer	nt canceling the				
7.  For purposes of appeal, the proposed amendment(s): a) [ how the new or amended claims would be rejected is prov The status of the claim(s) is (or will be) as follows: Claim(s) allowed:		be entered and an ex	xplanation of				
Claim(s) objected to: Claim(s) rejected: 1-8 and 12-13. Claim(s) withdrawn from consideration:							
AFFIDAVIT OR OTHER EVIDENCE							
<ol> <li>The affidavit or other evidence filed after a final action, but because applicant failed to provide a showing of good and was not earlier presented. See 37 CFR 1.116(e).</li> </ol>							
9. The affidavit or other evidence filed after the date of filing a entered because the affidavit or other evidence failed to or showing a good and sufficient reasons why it is necessary	vercome <u>all</u> rejections under appea	l and/or appellant fails	s to provide a				
10. ☐ The affidavit or other evidence is entered. An explanation REQUEST FOR RECONSIDERATION/OTHER	n of the status of the claims after er	ntry is below or attach	ed.				
<ol> <li>The request for reconsideration has been considered but see continuation sheet.</li> </ol>	does NOT place the application in	condition for allowan	ce because:				
<ul><li>12. ☐ Note the attached Information <i>Disclosure Statement</i>(s). (</li><li>13. ☐ Other:</li></ul>	PTO/SB/08) Paper No(s)						
/Alexa D. Neckel/	/S. G./						
Supervisory Patent Examiner, Art Unit 1795	Examiner, Art Unit 1795						

11. does NOT place the application in condition for allowance because:

Applicant argues that "Even if Nakajima is deemed to disclose the feature "the resistivity of the zinc oxide layer varying in the direction of its thickness" or specifically lowering the resistivity on the side of the zinc oxide in contact with an a-Si layer of one UPE with its other side in contact with a reflective metal layer..."(see pp 3 of Arguments).

The Examiner respectfully disagrees. Najakima is relied upon a general teaching of the concentration of metal impurities in a zinc oxide layer to be chosen based on the resistivity desired for the layer. Further, Nakajima teaches a non-uniform concentration of metal impurities such that the concentration can be "graded". It would have been obvious to one of ordinary skill in the art to try grading the metal impurity concentrations of the ZnO layer such that the resistivity of ZnO is higher on the surface with a UPE near a substrate than a resistivity of the ZnO layer in contact with a UPE farther from the substrate (see MPEP 2141 (III)).

Applicant argues that "[Mahan] does not at all discuss how the deposition rate and the deposition temperature may separately affect the formation of an ZnO layer to be used as an ITR layer in the stacking configuration of interest."

The Examiner respectfully disagrees. Mahan discloses deposition conditions for semiconductor devices, including temperature and deposition rate. Mahan further teaches that the temperature and deposition rate appear to control the hydrogen content of the film which affects the electrical properties of the individual layers and the device. It would have been obvious to one of ordinary skill in the art at the time of the invention to incorporation higher deposition techniques at lower temperatures as taught by Mahan to control the hydrogen content and thus controlling the properties of the layer.